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116 and ((remov\$4 or etch\$4)near10 trench\$4 )	1

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USPT	116 and ((remov\$4 or etch\$4)near10 trench\$4 )	1	<u>L17</u>
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USPT	16 and \$s7951	0	<u>L7</u>
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USPT	11 and 13	62	<u>L5</u>
USPT	photoresist or pattern\$4	511547	<u>L4</u>
USPT	12 or oxide or nitride	452697	<u>L3</u>
USPT	( (((borosilicate )or (borosilicate adj4 glass )or (borophosphosilicate adj4 glass ))or (TEOS )or (tetraethylorthosilicate ))or (hard adj3 mask\$3 )) or (BSG or BPSG ) )	25217	<u>L2</u>
USPT	( (((((((semiconduct\$4 )and (plasma near8 chamber ))and (wafer\$1 or substrate\$1 ))and (clamp\$4 ))and (electrode\$1 ))and (chlorine or "Cl.sub.2" ))and (("BCl.sub.3" )or (boron adj chloride )or (boron adj trichloride )))and (oxygen or (boron adj trichloride )))and (Argon or "Ar" )) and (nitrogen or "N.sub.2" ) )	62	<u>L1</u>